8-Bit Serial-Input/Parallel-Output Shift Register

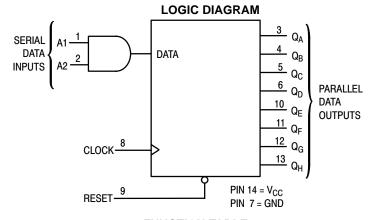
High-Performance Silicon-Gate CMOS

The MC74HC164A is identical in pinout to the LS164. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The MC74HC164A is an 8-bit, serial-input to parallel-output shift register. Two serial data inputs, A1 and A2, are provided so that one input may be used as a data enable. Data is entered on each rising edge of the clock. The active-low asynchronous Reset overrides the Clock and Serial Data inputs.

Features

- This device is manufactured with a Pb–Free external lead finish only*
- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 V to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 244 FETs or 61 Equivalent Gates



FUNCTION TABLE

Inputs					Outp	uts	
Reset	Clock	A 1	A2	Q_A	Q_B		Q _H
L	Х	Х	Χ	L	L		L
Н	~	Χ	Χ	No Change			
Н		Н	D	D	Q_{An}		Q_{Gn}
H		D	Н	D	Q_{An}		Q_Gn

D = data input

 $Q_{An} - Q_{Gn}$ = data shifted from the preceding stage on a rising edge at the clock input.



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MARKING DIAGRAMS



PDIP-14 N SUFFIX CASE 646 MC74HC164AN

AWLYYWW

1

14



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



= Assembly Location

WL or L = Wafer Lot YY or Y = Year WW or W = Work Week

PIN ASSIGNMENT

A1 [1 ●		v _{cc}
A2 [2	13	Q _H
Q _A [3	12] Q _G
Q _B [4	11	Q _F
Q _C [5	10	Q _E
Q_D	6	9	RESET
and [7	8	СГОСК

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC164AN	PDIP-14	2000 / Box
MC74HC164AD	SOIC-14	55 / Rail
MC74HC164ADR2	SOIC-14	2500 / Reel
MC74HC164ADT	TSSOP-14	96 / Rail
MC74HC164ADTR2	TSSOP-14	2500 / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to 0	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			V _{CC}	V
T _A	Operating Temperature, All Package Types			+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	–55°C to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	٧
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	>
V _{ОН}	Minimum High-Level Output Voltage	$\begin{split} &V_{in} = V_{IH} \text{ or } V_{IL} \\ & I_{out} \leq 20 \ \mu\text{A} \end{split}$ $&V_{in} = V_{IH} \text{ or } V_{IL} \qquad \begin{aligned} & I_{out} \leq 2.4 \text{ mA} \\ & I_{out} \leq 4.0 \text{ mA} \\ & I_{out} \leq 5.2 \text{ mA} \end{aligned}$	2.0 4.5 6.0 3.0 4.5 6.0	1.9 4.4 5.9 2.48 3.98 5.48	1.9 4.4 5.9 2.34 3.84 5.34	1.9 4.4 5.9 2.20 3.70 5.20	>

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	v _{cc}	-55°C to 25°C	≤ 85°C	≤ 125°C	Unit
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & I_{\text{out}} \leq 2.4 \text{ mA} \\ I_{\text{out}} \leq 4.0 \text{ mA} \\ I_{\text{out}} \leq 5.2 \text{ mA} \end{split}$	4.5	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

			Guaranteed Limit		mit		
Symbol	Parameter		–55°C to 25°C	≤ 85°C	≤ 125°C	Unit	
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 3.0 4.5 6.0	10 20 40 50	10 20 35 45	10 20 30 40	MHz	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	2.0 3.0 4.5 6.0	160 100 32 27	200 150 40 34	250 200 48 42	ns	
t _{PHL}	Maximum Propagation Delay, Reset to Q (Figures 2 and 4)	2.0 3.0 4.5 6.0	175 100 35 30	220 150 44 37	260 200 53 45	ns	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns	
C _{in}	Maximum Input Capacitance		10	10	10	pF	

NOTES:

^{2.} Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	180	рF

^{*} Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

^{1.} For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

			Gu	aranteed Li	mit	
Symbol	Parameter	v _{cc} v	–55°C to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, A1 or A2 to Clock (Figure 3)	2.0 3.0 4.5 6.0	25 15 7 5	35 20 8 6	40 25 9 6	ns
t _h	Minimum Hold Time, Clock to A1 or A2 (Figure 3)	2.0 3.0 4.5 6.0	3 3 3 3	3 3 3 3	3 3 3 3	ns
t _{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	3 3 3 3	3 3 3 3	3 3 3 3	ns
t _w	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	50 26 12 10	60 35 15 12	75 45 20 15	ns
t _w	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	50 26 12 10	60 35 15 12	75 45 20 15	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS

A1, A2 (Pins 1, 2)

Serial Data Inputs. Data at these inputs determine the data to be entered into the first stage of the shift register. For a high level to be entered into the shift register, both A1 and A2 inputs must be high, thereby allowing one input to be used as a data—enable input. When only one serial input is used, the other must be connected to $V_{\rm CC}$.

Clock (Pin 8)

Shift Register Clock. A positive—going transition on this pin shifts the data at each stage to the next stage. The shift

register is completely static, allowing clock rates down to DC in a continuous or intermittent mode.

OUTPUTS

Q_A - Q_H (Pins 3, 4, 5, 6, 10, 11, 12, 13)

Parallel Shift Register Outputs. The shifted data is presented at these outputs in true, or noninverted, form.

CONTROL INPUT

Reset (Pin 9)

Active–Low, Asynchronous Reset Input. A low voltage applied to this input resets all internal flip–flops and sets Outputs $Q_A - Q_H$ to the low level state.

SWITCHING WAVEFORMS

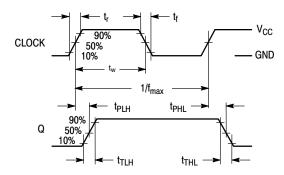


Figure 1.

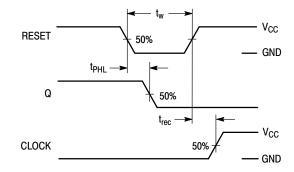


Figure 2.

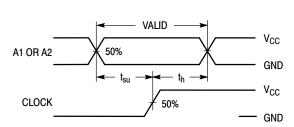
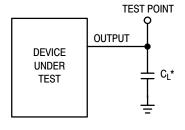


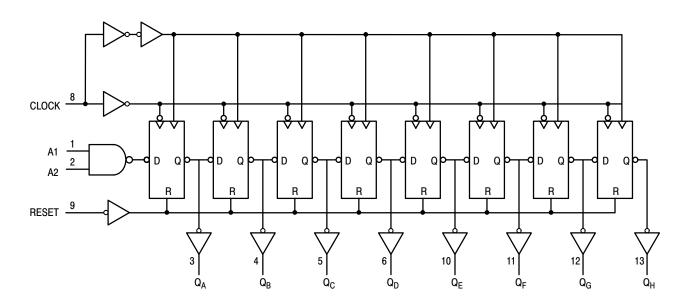
Figure 3.



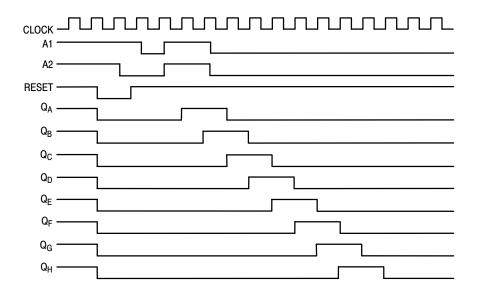
*Includes all probe and jig capacitance

Figure 4. Test Circuit

EXPANDED LOGIC DIAGRAM

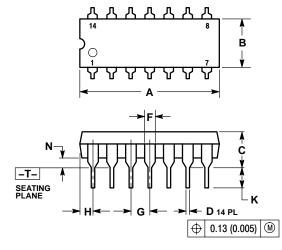


TIMING DIAGRAM



PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE N

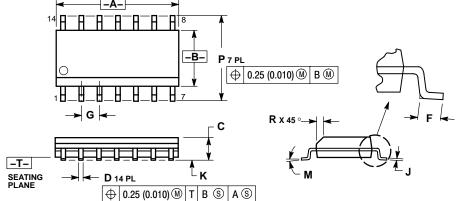




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE
- MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	18.80
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
٦	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
М		10 °		10 °
N	0.015	0.039	0.38	1.01

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE G**

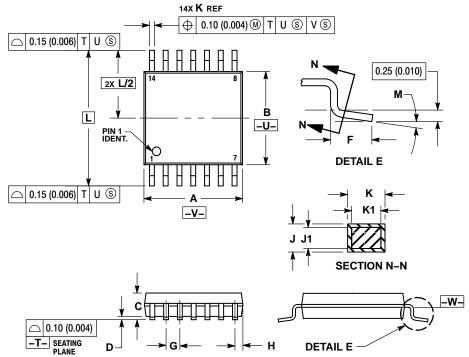


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) DEB 1018.
- PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
М	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE O**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH,
 PROTRUSIONS OR GATE BURRS. MOLD FLASH
 OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED
- PROTHUSION STALL NOT EXCEED
 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
٦	6.40 BSC		0.252 BSC	
М	0°	8°	0°	8°

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